

In the Specification:

Please amend paragraph [0008] as follows:

[0008] To illustrate the above-outlined problem in further detail, a view from Figure 2A is depicted diagrammatically in Figure 2B. Two wells, namely an n-type well 11 and a p-type well 12, lie next to one another and are separated by a boundary labeled with G1 at the top of the figure and with G2 at the bottom of the figure. As already described with reference to Figure 1, during the implantation of n-type well 11, p-type well 12 is covered by a WP resist 3. Due to the scattering radiation at the edge of the WP resist layer, in the manner outlined above, the active components are doped undesirably and influenced in a harmful manner in an edge region 13 of n-type well 11 which faces side a2 of p-type well. In the example illustrated with reference to Figures 2A and 2B, the undesirable doping applies to the active structures in n-type well 11 that lie below the line of symmetry S in the drawing, but, on account of the symmetry property, not to the corresponding active circuit structures in an n-type well 11 lying above the line of symmetry S.